SPICE Device Model SUM110P04-05
Vishay Siliconix

P-Channel 40-V (D-S) MOSFET

CHARACTERISTICS

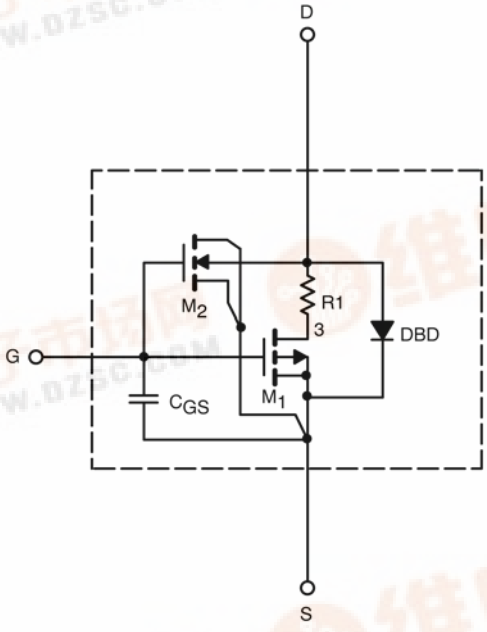
- P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the −55 to 125°C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

DESCRIPTION

The attached spice model describes the typical electrical characteristics of the p-channel vertical DMOS. The subcircuit model is extracted and optimized over the −55 to 125°C temperature ranges under the pulsed 0-V to 10-V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

SUBCIRCUIT MODEL SCHEMATIC



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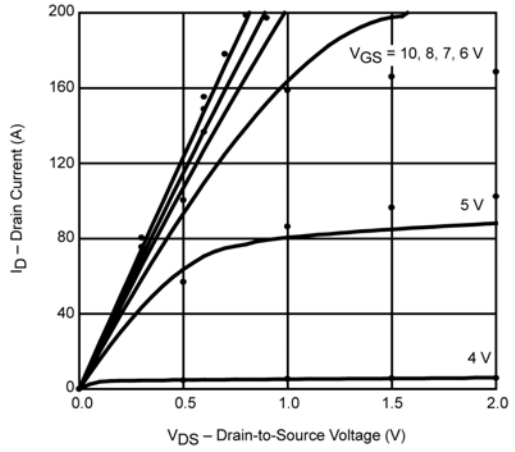
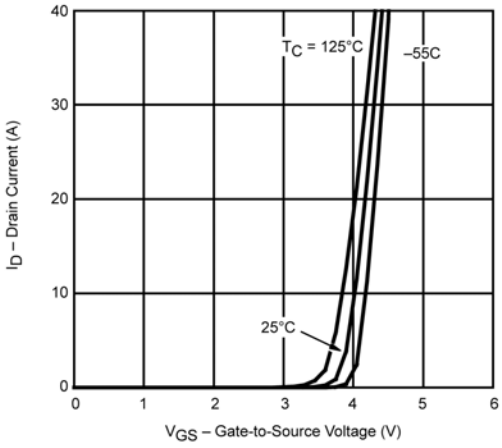
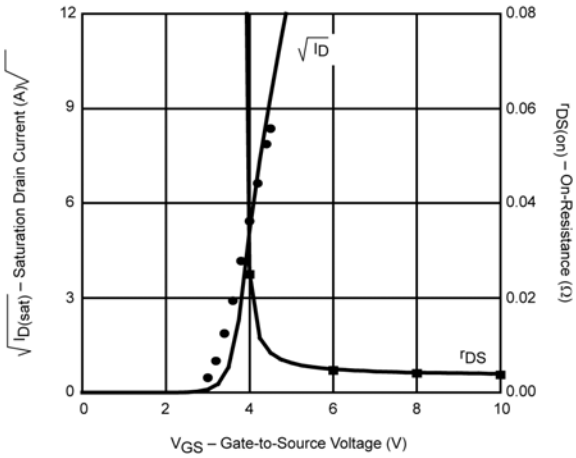
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)					
Parameter	**Symbol**	**Test Condition**	**Simulated Data**	**Measured Data**	**Unit**
Static					
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = – 250 μA	2.8		V
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ –5 V, V_{GS} = –10 V	982		A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = –10 V, I_D = –20 A	0.0040	0.0041	Ω
Forward Transconductance[a]	g_{fs}	V_{DS} = –15 V, I_D = –20 A	126	75	S
Diode Forward Voltage[a]	V_{SD}	I_S = –20 A	–0.88	–80	V
Dynamic[b]					
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = –25 V, f = 1 MHz	9687	11300	pF
Output Capacitance	C_{oss}		1524	1510	
Reverse Transfer Capacitance	C_{rss}		844	1000	
Total Gate Charge[c]	Q_g	V_{DS} = –20 V, V_{GS} = –10 V, I_D = –20 A	195	185	nC
Gate-Source Charge[c]	Q_{gs}		48	48	
Gate-Drain Charge[c]	Q_{gd}		42	42	

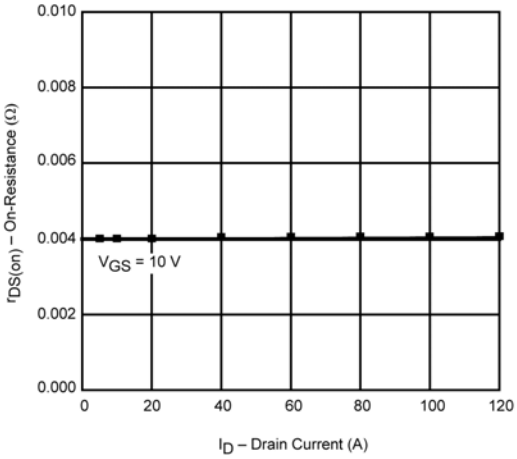
Notes
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

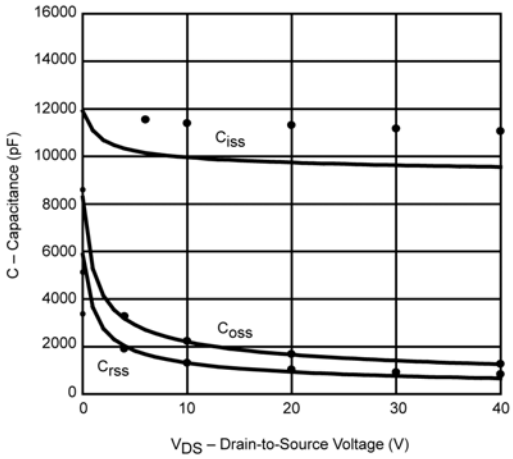
COMPARISON OF MODEL WITH MEASURED DATA (T_J=25°C UNLESS OTHERWISE NOTED)

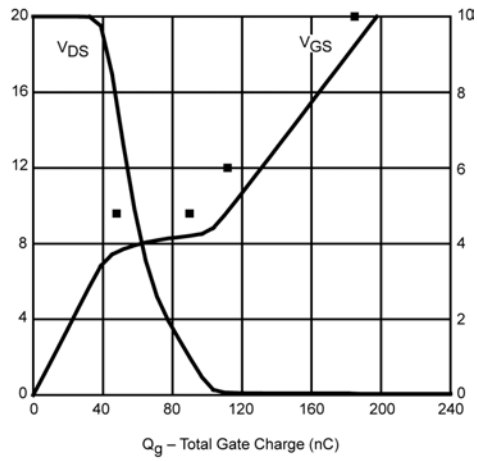












Note: Dots and squares represent measured data.